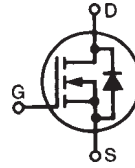


**HiperFET™**  
**Power MOSFET**  
**Q3-Class**

**IXFN44N80Q3**

$V_{DSS} = 800V$   
 $I_{D25} = 37A$   
 $R_{DS(on)} \leq 190m\Omega$   
 $t_{rr} \leq 300ns$

N-Channel Enhancement Mode  
 Fast Intrinsic Rectifier  
 Avalanche Rated



miniBLOC  
 E153432



G = Gate      D = Drain  
 S = Source

Either Source Terminal S can be used as the Source Terminal or the Kelvin Source (Gate Return) Terminal.

| Symbol        | Test Conditions  | Maximum Ratings |            |
|---------------|--|-----------------|------------|
| $V_{DSS}$     | $T_J = 25^\circ C$ to $150^\circ C$                                | 800             | V          |
| $V_{DGR}$     | $T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$          | 800             | V          |
| $V_{GSS}$     | Continuous   | $\pm 30$        | V          |
| $V_{GSM}$     | Transient  | $\pm 40$        | V          |
| $I_{D25}$     | $T_C = 25^\circ C$   | 37              | A          |
| $I_{DM}$      | $T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$               | 130             | A          |
| $I_A$         | $T_C = 25^\circ C$   | 44              | A          |
| $E_{AS}$      | $T_C = 25^\circ C$   | 3.5             | J          |
| $dv/dt$       | $I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$ | 50              | V/ns       |
| $P_D$         | $T_C = 25^\circ C$   | 780             | W          |
| $T_J$         |  | -55 ... +150    | $^\circ C$ |
| $T_{JM}$      |  | 150             | $^\circ C$ |
| $T_{stg}$     |  | -55 ... +150    | $^\circ C$ |
| $V_{ISOL}$    | 50/60 Hz, RMS, $t = 1$ minute                                      | 2500            | V~         |
|               | $I_{ISOL} \leq 1mA$ , $t = 1s$                                     | 3000            | V~         |
| $M_d$         | Mounting Torque for Base Plate                                     | 1.5/13          | Nm/lb.in.  |
|               | Terminal Connection Torque   | 1.3/11.5        | Nm/lb.in.  |
| <b>Weight</b> |  | 30              | g          |

**Features**

- International Standard Package
- Low Intrinsic Gate Resistance
- miniBLOC with Aluminum Nitride Isolation
- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Rectifier
- Low  $R_{DS(on)}$  and  $Q_G$

**Advantages**

- High Power Density
- Easy to Mount
- Space Savings

**Applications**

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- DC Choppers
- Temperature and Lighting Controls

| Symbol       | Test Conditions<br>( $T_J = 25^\circ C$ Unless Otherwise Specified) | Characteristic Values |      |                      |
|--------------|---|-----------------------|------|----------------------|
|              |   | Min.                  | Typ. | Max.                 |
| $BV_{DSS}$   | $V_{GS} = 0V$ , $I_D = 3mA$   | 800                   |      | V                    |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 8mA$                                     | 3.5                   |      | 6.5 V                |
| $I_{GSS}$    | $V_{GS} = \pm 30V$ , $V_{DS} = 0V$                                  |                       |      | $\pm 200$ nA         |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$ , $V_{GS} = 0V$<br>$T_J = 125^\circ C$           |                       |      | 50 $\mu A$<br>2.5 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V$ , $I_D = 22A$ , Note 1                               |                       |      | 190 m $\Omega$       |

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)   | Characteristic Values |       |  |
|--------------|---|-----------------------|-------|--|
|              |   | Min.                  | Typ.  | Max.   |
| $g_{fs}$     | $V_{DS} = 20\text{V}, I_D = 22\text{A}$ , Note 1  | 22                    | 37    | S  |
| $C_{iss}$    | $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$  |                       | 10950 | pF   |
| $C_{oss}$    |   |                       | 957   | pF   |
| $C_{rss}$    |   |                       | 95    | pF   |
| $R_{Gi}$     | Gate Input Resistance   |                       | 0.20  | $\Omega$                                     |
| $t_{d(on)}$  | <b>Resistive Switching Times</b><br>$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 22\text{A}$<br>$R_G = 1\Omega$ (External) |                       | 45    | ns   |
| $t_r$        |   |                       | 60    | ns   |
| $t_{d(off)}$ |   |                       | 63    | ns   |
| $t_f$        |   |                       | 20    | ns   |
| $Q_{g(on)}$  | $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 22\text{A}$   |                       | 185   | nC   |
| $Q_{gs}$     |   |                       | 67    | nC   |
| $Q_{gd}$     |   |                       | 83    | nC   |
| $R_{thJC}$   |   |                       | 0.05  | $0.16^\circ\text{C/W}$<br>$^\circ\text{C/W}$ |
| $R_{thCS}$   |   |                       |       |  |

### Source-Drain Diode

| Symbol   | Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)                       | Characteristic Values |      |               |
|----------|---|-----------------------|------|---------------|
|          |   | Min.                  | Typ. | Max.          |
| $I_s$    | $V_{GS} = 0\text{V}$  |                       |      | 44 A          |
| $I_{SM}$ | Repetitive, Pulse Width Limited by $T_{JM}$   |                       |      | 176 A         |
| $V_{SD}$ | $I_F = I_s, V_{GS} = 0\text{V}$ , Note 1  |                       |      | 1.4 V         |
| $t_{rr}$ | $I_F = 22\text{A}, -di/dt = 100\text{A}/\mu\text{s}$<br>$V_R = 100\text{V}, V_{GS} = 0\text{V}$ |                       | 1.8  | 300 ns        |
| $Q_{RM}$ |   |                       |      | $\mu\text{C}$ |
| $I_{RM}$ |   |                       |      | A             |

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

### SOT-227B (IXFN) Outline

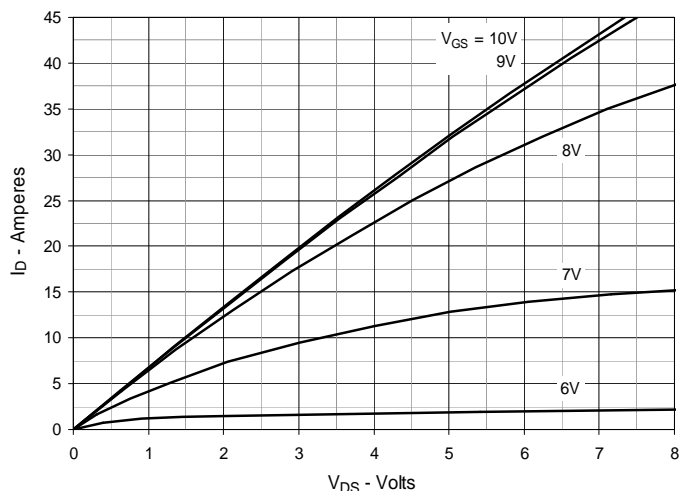
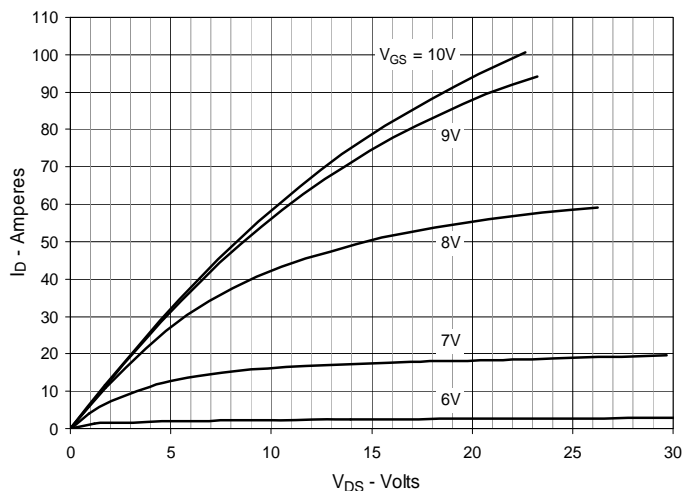
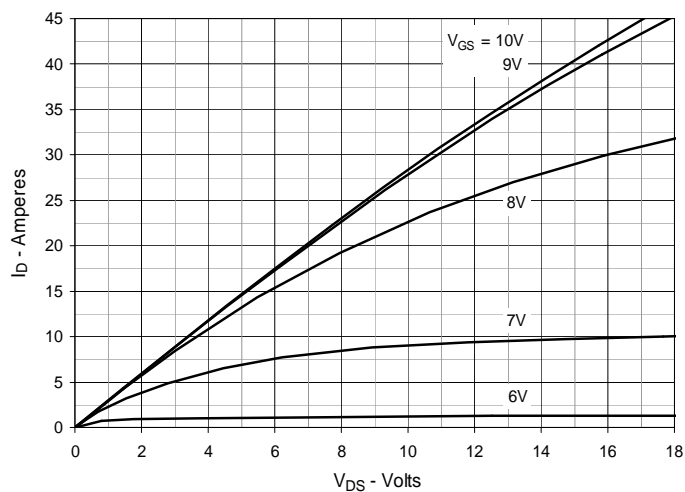
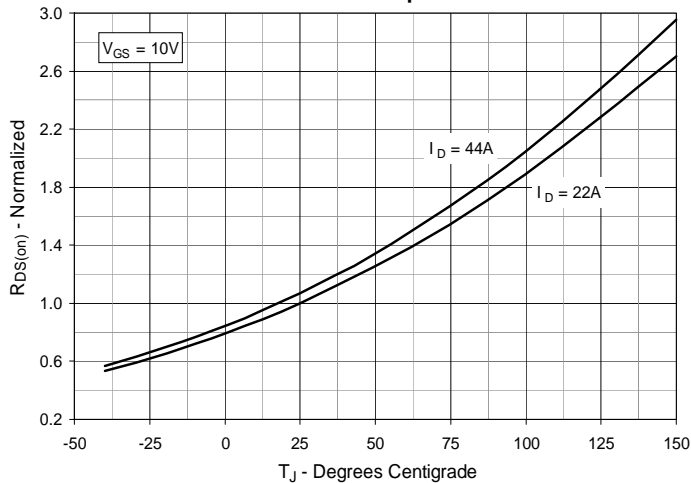
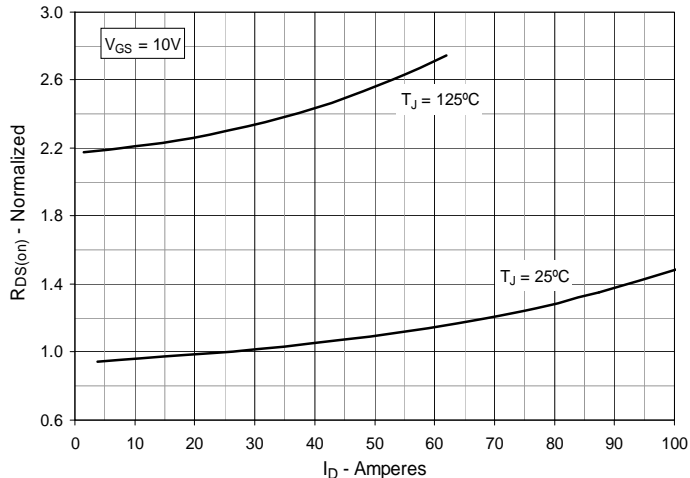
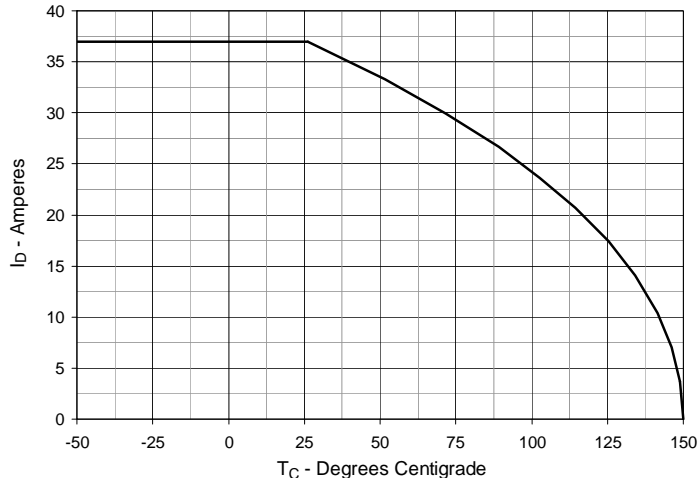


(M4 screws (4x) supplied)

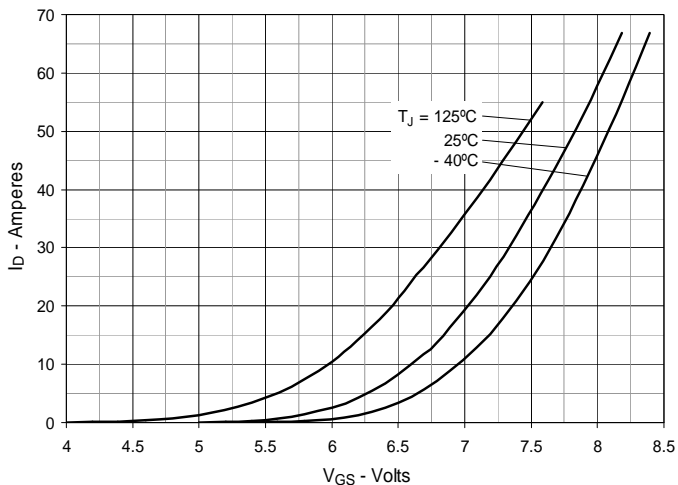
| SYM | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
|     | MIN    | MAX   | MIN         | MAX   |
| A   | 1.240  | 1.255 | 31.50       | 31.88 |
| B   | .307   | .323  | 7.80        | 8.20  |
| C   | .161   | .169  | 4.09        | 4.29  |
| D   | .161   | .169  | 4.09        | 4.29  |
| E   | .161   | .169  | 4.09        | 4.29  |
| F   | .587   | .595  | 14.91       | 15.11 |
| G   | 1.186  | 1.193 | 30.12       | 30.30 |
| H   | 1.496  | 1.505 | 38.00       | 38.23 |
| J   | .460   | .481  | 11.68       | 12.22 |
| K   | .351   | .378  | 8.92        | 9.60  |
| L   | .030   | .033  | 0.76        | 0.84  |
| M   | .496   | .506  | 12.60       | 12.85 |
| N   | .990   | 1.001 | 25.15       | 25.42 |
| O   | .078   | .084  | 1.98        | 2.13  |
| P   | .195   | .235  | 4.95        | 5.97  |
| Q   | 1.045  | 1.059 | 26.54       | 26.90 |
| R   | .155   | .174  | 3.94        | 4.42  |
| S   | .186   | .191  | 4.72        | 4.85  |
| T   | .968   | .987  | 24.59       | 25.07 |
| U   | -.002  | .004  | -0.05       | 0.1   |

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

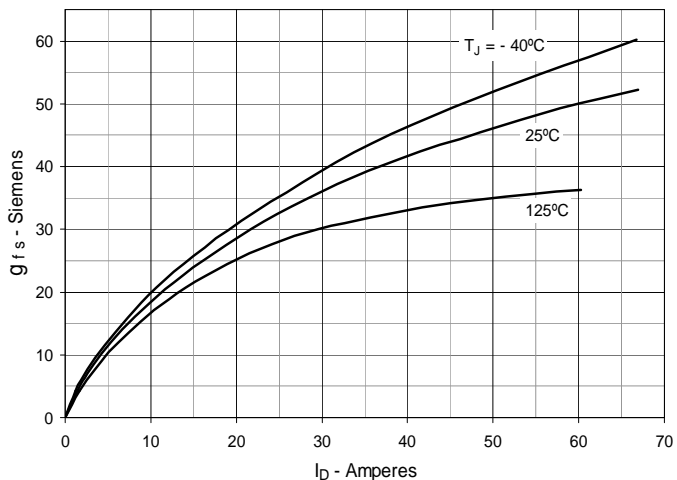
|  |           |           |           |           |              |              |              |              |              |             |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665    | 6,404,065 B1 | 6,683,344    | 6,727,585    | 7,005,734 B2 | 7,157,338B2 |
|  | 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343    | 6,710,405 B2 | 6,759,692    | 7,063,975 B2 |             |
|  | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505    | 6,710,463    | 6,771,478 B2 | 7,071,537    |             |

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$** 

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 22\text{A}$  Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 22\text{A}$  Value vs. Drain Current**

**Fig. 6. Maximum Drain Current vs. Case Temperature**


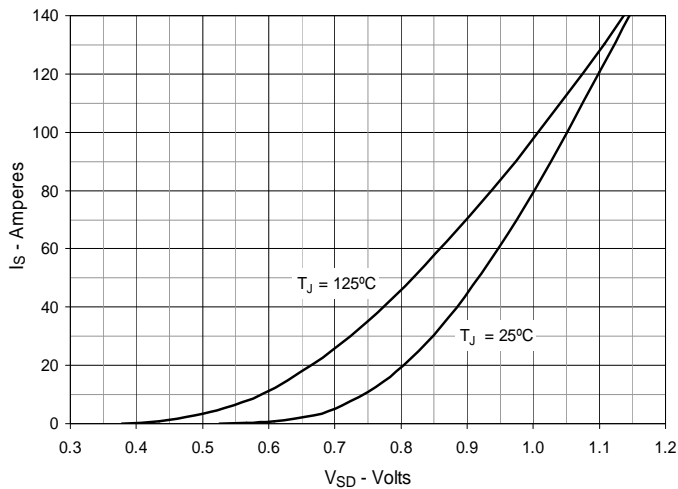
**Fig. 7. Input Admittance**



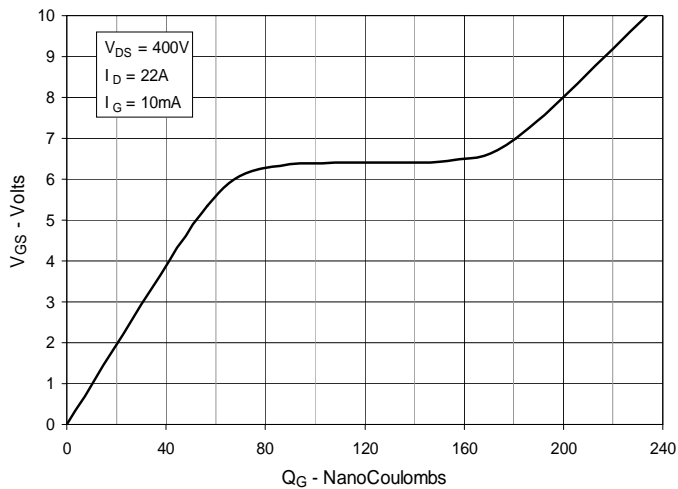
**Fig. 8. Transconductance**



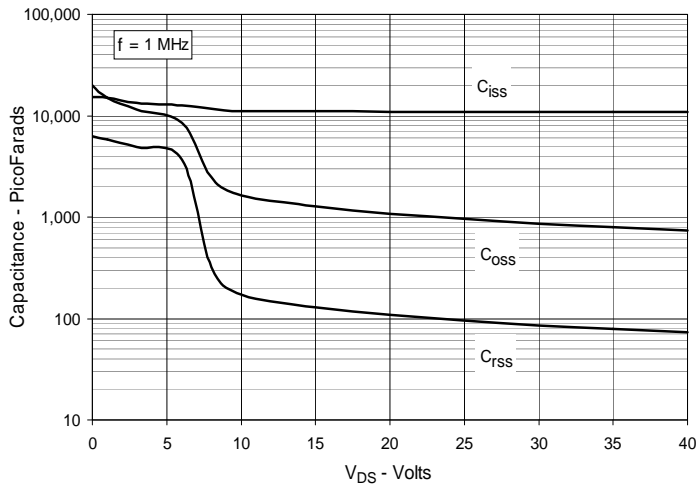
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**

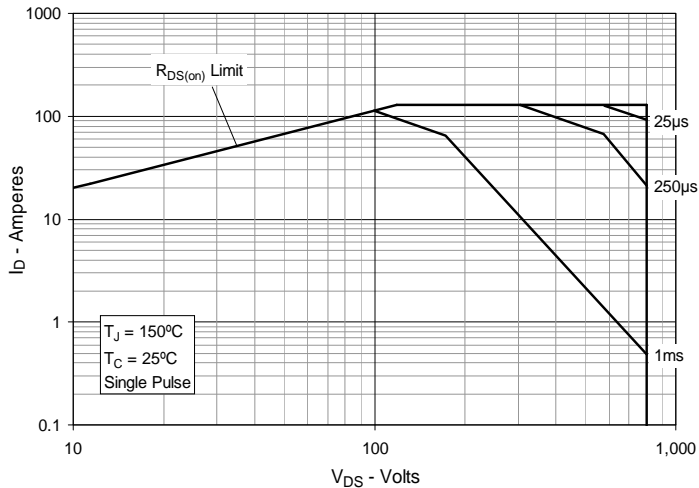


Fig. 13. Maximum Transient Thermal Impedance

